MMBD204SEW

SILICON EPITAXIAL PLANAR SWITCHING DIODE

Applications

• Ultra high speed switching





SOT-323 Plastic Package Marking Code: A7

Absolute Maximum Ratings (T_a = 25 °C)

Parameter	Symbol	Value	Unit
Repetitive Peak Reverse Voltage	V_{RM}	20	V
Reverse Voltage	V_R	20	V
Average Rectified Forward Current	Io	100	mA
Maximum (Peak) Forward Current (Single)	I _{FM}	200	mA
Peak Forward Surge Current (t _p = 1 μs)	I _{FSM}	300	mA
Power Dissipation	P _d	200	mW
Junction Temperature	TJ	150	°C
Storage Temperature Range	Ts	- 55 to + 150	°C

Characteristics at T_a = 25 °C

Parameter	Symbol	Max.	Unit
Forward Voltage at I _F = 10 mA	V _F	1	V
Reverse Current at $V_R = 15 \text{ V}$	I _R	0.1	μΑ
Capacitance between Terminals at $V_R = 6$, $f = 1$ MHz	Ст	4	pF





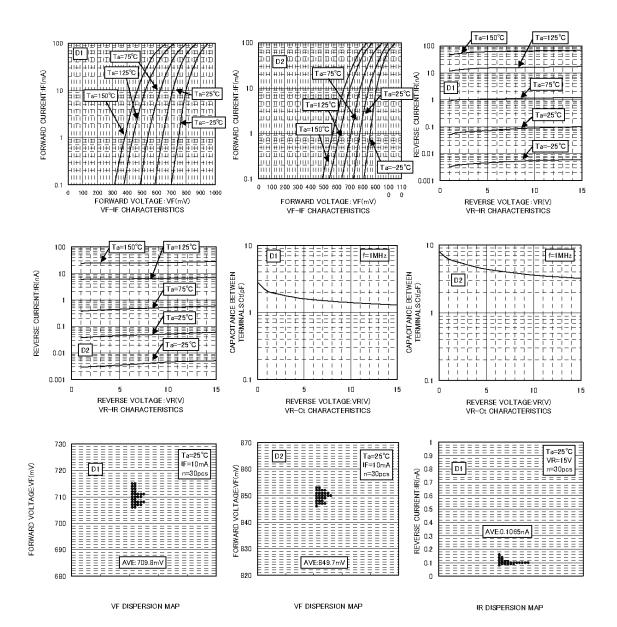
(Subsidiary of Sino-Tech International Holdings Limited, a company listed on the Hong Kong Stock Exchange, Stock Code: 724)







Dated: 10/10/2008





SEMTECH ELECTRONICS LTD.

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ISO/TS 16949 : 2002 | | Certificate No. 05103 | C

ISO 14001:2004 ISC Certificate No. 7116 Cert